



1/28/06 2856

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of:	)	Group Art Unit: 2856
Doll et al.	)	Examiner: Not yet assigned
	)	
Title: MICRO-STRUCTURED GAS SENSOR	)	
WITH CONTROL OF GAS SENSITIVE	)	
PROPERTIES BY APPLICATION OF AN	)	
ELECTRICAL FIELD	)	
	)	
Serial No.: 10/507,054	)	
	)	
Filed: September 9, 2004	)	Our Docket No. 7745

Springfield, Massachusetts

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Dear Sir:

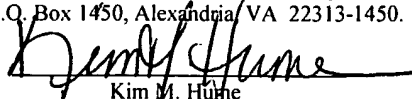
Applicant(s) submits herewith Form PTO-1449 identifying patents, publications or other information of which they are aware, which they believe may be material to the examination of this application and in respect of which there may be a duty to disclose.

The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made (37 CFR 1.97(g)), an admission that the information cited is, or is considered to be, material to patentability, or that no other material information exists.

The filing of this Information Disclosure Statement shall not be construed as an admission against interest in any manner. Notice of January 9, 1992, 1135 O.G. 13-25, at 25.

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I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

  
Kim M. Hume

9/28/06  
Date

Application Serial No.: 10/507,054  
Docket No. 7745

Under 37 CFR 1.97 (b)

☒ This Information Disclosure Statement is being filed within three months of the filing date of the application, or the date of entry into the national stage of an international application, or before the mailing date of a first Office Action on the merits, whichever event occurs last, or before the mailing of a first Office Action after the filing of a Request for Continued Examination under § 1.114.

Under 37 CFR 1.97 (c)

☐ This Information Disclosure Statement is being filed *after* three months of the filing date of this national application, or the date of entry into the national stage as set forth in §1.491 in an international application, or after the mailing date of the first Office Action on the merits, whichever event occurred last, but *before* the mailing date of either a final action under §1.113 or a notice of allowance under §1.311, whichever occurs first.

- ☐ A certification as specified in 37 CFR 1.97(e) is set forth below, or
- ☐ Fee as set forth in 37 CFR 1.17(p) (\$180.00).

Under 37 CFR 1.97(d)

☐ This Information Disclosure Statement is being filed *after* a final action under §1.113 or a notice of allowance under §1.311, whichever occurs first, but before, or simultaneously with, the payment of the issue fee. Applicant hereby petitions for the consideration of this Information Disclosure Statement, 37 CFR 1.97(d)(ii). A certification as specified in 37 CFR 1.97(e) is set forth below.

- ☐ A certification as specified in 37 CFR 1.97(e) is set forth below, and
- ☐ Fee as set forth in 37 CFR 1.17(p) (\$180.00)

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**CERTIFICATION (37 CFR 1.97(e))**

☐ Each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement. A copy of the relevant search report is enclosed herewith.

☐ No item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing this certification after making reasonable inquiry, no item of information contained in the Information Disclosure Statement was known to any individual designated in §1.56(c) more than three months prior to the filing of this Statement.

Application Serial No.: 10/507,054  
Docket No. 7745

Applicants respectfully request that any deficiencies in the fees be charged to Deposit  
Order Account No. 50-3381.

Respectfully submitted,

By: 

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7745

APPLICANT: Doll et al.

FILING DATE: September 9, 2004

SERIAL NO. 10/507,054

GROUP: 2856

EXAMINER: Not yet assigned

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT****U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A						
	B						
	C						
	D						

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	E						
	F						
	G						
	H						

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

EXAMINER INITIAL		
	I	D. Williams, "Semiconducting oxides as gas-sensitive resistors," Sensors and Actuators B: Chemical B 57 (1-2) (1999) 1-27.
	J	Simon et al., "Micromachined metal oxide gas sensors: opportunities to improve sensor performance,," Sensors and Actuators B 73 (2001) 1-26.
	K	H. Geistlinger, "Electron theory of thin-film gas sensors," Sensors and Actuators B 17 (1993) 47-60.
	L	Lundström et al., "A hydrogen-sensitive MOS field-effect transistor," Applied Physics Letters, Vol. 26, No. 2, 1975, pp. 55-57.
	M	P.B. Weisz, "Effects of electronic transfer between adsorbate and solid on chemisorption and catalysis," The Journal of Chemical Physics, Vol. 21, No. 9, 1953, pp. 1531-1538.
	N	T. Wolkenstein, "Electronic Processes on Semiconductor Surfaces during Chemisorption," Consultants Bureau, New York & London, 1991.
	O	Hoenig et al., "Chemisorption of Oxygen on Zinc Oxide, Effect of a DC Electric Field," Surface Science 11 (1968) 163-174.
	P	Comini et al., "Light enhanced gas sensing properties of indium oxide and tin dioxide sensors," Sensors and Actuators B: Chemical 65 (1-3) (2000) pp. 260-263.
	Q	Popova et al., "Voltage dependence gas-sensing behaviour of SnO <sub>2</sub> -gate FETs," Sensors and Actuators B: 18- 19 (1994) 543-545.

**EXAMINER****DATE CONSIDERED****EXAMINER:**

**Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.**